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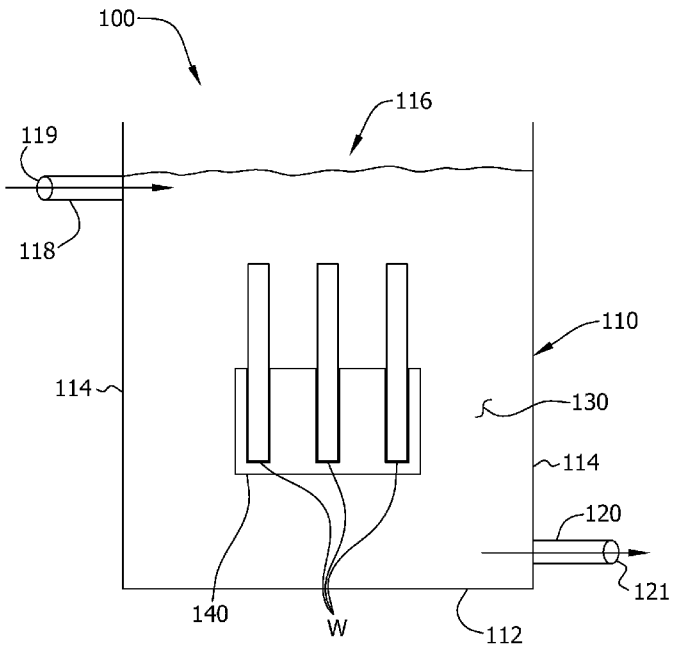
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(54) Title: METHODS FOR ANALYSIS OF WATER AND SUBSTRATES RINSED IN WATER

FIG. 1



(57) Abstract: Methods are disclosed for predicting the amount of contaminants deposited on a substrate, such as a semiconductor wafer (W), after contacting the wafer with water in a container. The contaminants may include materials that negatively affect the properties of the wafer even when the amount of contaminants deposited on the surface of the wafer is below the threshold level of detection of known systems. The method includes contacting the wafer with water for a first period of time, the wafer having wafer surfaces, drying the wafer, analyzing the wafer to determine contaminants on the wafer surfaces, and predicting the amount of contaminants deposited on the wafer when contacting the wafer with water for a second period of time shorter than the first period of time.

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